

PNP SILICON DARLINGTONS POWER TRANSISTORS

They are silicon epitaxial base transistors mounted in TO-3PN. They are designed for audio output stages and general amplifier and switching applications. complementary is BDV65-A-B-C Compliance to RoHS.

ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings		Value	Unit
		BDV64	-60	
.,	Collector-Emitter Voltage	BDV64A	-80	\ /
V _{CEO}		BDV64B	-100	V
		BDV64C	-120	
		BDV64	-60	
V	Callacter Dage Voltage	BDV64A	-80	V
V _{CBO}	Collector-Base Voltage	BDV64B	-100	
		BDV64C	-120	
		BDV64		V
V	Emitter Rose Voltage	BDV64A	-5.0	
V _{EBO}	Emitter-Base Voltage	BDV64B	-5.0	
		BDV64C		
		BDV64		A
Ic	Collector Current	BDV64A	-12	
ıc		BDV64B	-12	
		BDV64C		
Ісм		BDV64		
	Collector Peak Current	BDV64A	-15	
		BDV64B	13	
		BDV64C		
		BDV64		
I _B	Base Current	BDV64A	-0.5	А
IB		BDV64B		
		BDV64C		



ABSOLUTE MAXIMUM RATINGS

Symbol	Ratings			Value	Unit
	Power Dissipation		BDV64		
		T _ 25°C	BDV64A	125	
		$T_{mb} = 25^{\circ}C$	BDV64B	125	
В			BDV64C		· W
P _T			BDV64		VV
		$T_{mb} = 25^{\circ}C$	BDV64A	3.5	
		1 _{mb} = 25 C	BDV64B	3.5	
		 	BDV64C		
TJ			BDV64		
	Junction Temperature		BDV64A	150	
			BDV64B	150	
			BDV64C		C
T _S			BDV64		C
	Storage Temperature		BDV64A	-65 to +150	
			BDV64B	-05 10 +150	
			BDV64C		

THERMAL CHARACTERISTICS

Symbol	Ratings	Value	Unit	
		BDV64		
R _{thj-c}	Thermal Desigtance Junction to Coop	BDV64A	4	90 / W/
	Thermal Resistance, Junction to Case	BDV64B	ı	
		BDV64C		
R _{thj-a}		BDV64		~ ℃/W
	Thormal Desigtance Junction to Ambient	BDV64A	25.7	
	Thermal Resistance, Junction to Ambient	BDV64B	35.7	
		BDV64C		



ELECTRICAL CHARACTERISTICS

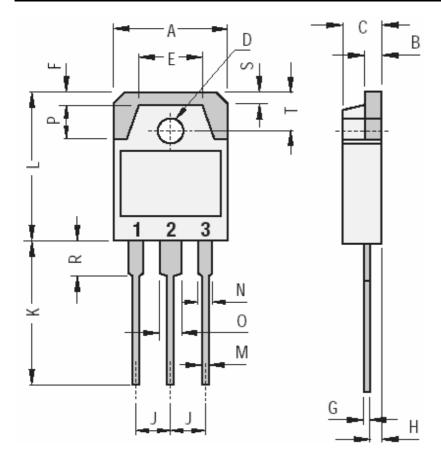
TC=25℃ unless otherwise noted

Symbol	Ratings	Test Condition(s)		Min	Тур	Max	Unit	
		V _{CE} = -30 V	′, I _B = 0	BDV64				
I _{CEO}	Collector Cutoff Current	$V_{CE} = -40 \text{ V}, I_{B} = 0$		BDV64A	-	-	-2	mA
		V_{CE} = -50 V, I_{B} = 0 V_{CE} = -60 V, I_{B} = 0		BDV64B				
				BDV64C				
	Freitter Cuteff Current	V _{BE} = -5 V, I _C = 0		BDV64	-	-	-5	mA
				BDV64A				
I _{EBO}	Emitter Cutoff Current			BDV64B				
				BDV64C	1			
			V _{CB} = -60 V	BDV64		-		
		I _E = 0 T _j =25℃	V _{CB} = -80 V	BDV64A	_		-0.4	mA
			V _{CB} = -100 V	BDV64B				
١.	Collector Cutoff		V _{CB} = -120 V	BDV64C				
I _{CBO}	Current	I _E = 0 T _j =150℃	V _{CB} = -30 V	BDV64		-	-2	
			V _{CB} = -40 V	BDV64A	- - -			
			V _{CB} = -50 V	BDV64B				
			V _{CB} = -60 V	BDV64C				
	Collector-Emitter Breakdown Voltage (*)	I_{C} = -30 mA, I_{B} = 0		BDV64	-60	-	-	- V
.,				BDV64A	-80	-		
V _{CEO}				BDV64B	-100	-	-	
				BDV64C	-120	-	-	
	DC Current Gain (*)			BDV64			-	-
l.		$V_{CE} = -4 \text{ V}, I_{C} = -5 \text{ A}$		BDV64A	1000	-		
h _{FE}				BDV64B				
				BDV64C				
	Collector-Emitter saturation Voltage (*)		BDV64	-	-	-2	V	
V _{CE(SAT)}		I _C = -5 A, I _B = -20 mA						BDV64A
								BDV64B
								BDV64C
V _{BE}	Base-Emitter Voltage(*)			BDV64				
		V _{CE} = -4 V, I _C = -5 A BDV64A BDV64B			2.5			
]	-	-2,5	V
				BDV64C				

^(*) Pulse Width $\approx 300~\mu s,$ Duty Cycle \angle 1.5 %



MECHANICAL DATA CASE TO3PN Non Isolated Plastic Package



DIMENSIONS (mm)					
	Min.	Max.			
Α	15.20	1600			
В	1.90	2.10			
С	4.60	5.00			
B C D E F	3.10	3.30			
Е		9.60			
F		2.00			
G H J K	0.35				
Н		1.40			
J	5.35	5.55			
K	20.00)			
L M	19.60	20.20			
М	0.95				
N		2.00			
O P		3.00			
		4.00			
R		4.00			
R S T		1.80			
Т	4.80	5.20			
Pin 1	Pin 1 : Base				
Pin 2	:	Collector			

Pin 1 : Base Pin 2 : Collector Pin 3 : Emitter Package Collector

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www.comsetsemi.com

info@comsetsemi.com